



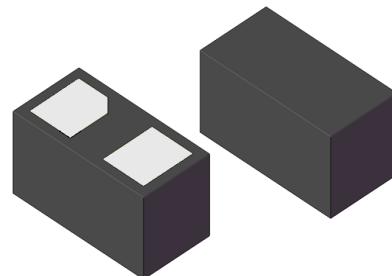
RHONDA TEK

RHONDA SEMICONDUCTOR CO.,LTD

RHTVSUC0521N-S
Transient Voltage Suppressing Device
For ESD/Transient Protection

Features

- 100Watts peak pulse power ($t_p = 8/20\mu s$)
- Tiny DFN1006 package
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance ($C_j=0.2\text{pF}$ typ.)
- Protection one data/power line to:
 - IEC 61000-4-2 $\pm 10\text{kV}$ contact $\pm 15\text{kV}$ air
 - IEC 61000-4-4 (EFT) 40A (5/50ns)
 - IEC 61000-4-5 (Lightning) 4A (8/20 μs)



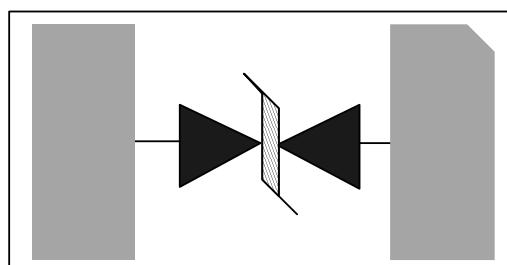
Applications

- Cell Phone Handsets and Accessories
- Microprocessor based equipment
- Personal Digital Assistants (PDA's)
- Notebooks, Desktops, and Servers
- Portable Instrumentation

Mechanical Data

- DFN1006 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

Schematic & PIN Configuration



DFN1006



Absolute Maximum Rating

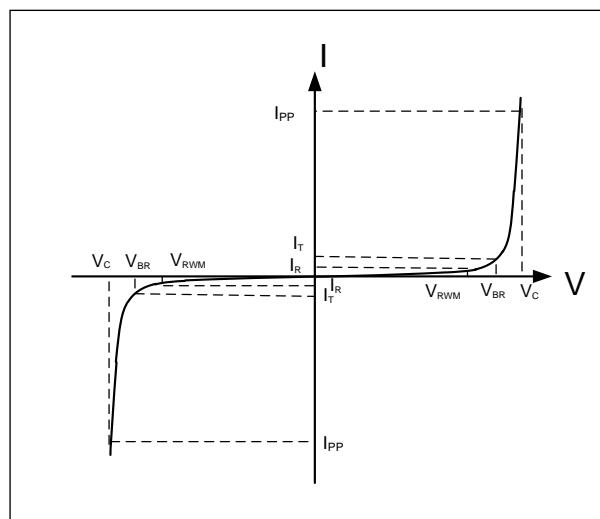
Rating	Symbol	Value	Units
Peak Pulse Power ($t_p = 8/20\mu s$)	P_{PP}	100	Watts
Peak Pulse Current ($t_p = 8/20\mu s$) (note1)	I_{PP}	4	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V_{ESD}	15 10	kV
Lead Soldering Temperature	T_L	260(10seconds)	°C
Junction Temperature	T_J	-55 to + 125	°C
Storage Temperature	T_{stg}	-55 to + 125	°C

Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{RWM}				5.0	V
Reverse Breakdown Voltage	V_{BR}	$I_T=1mA$	6.0	7.5		V
Reverse Leakage Current	I_R	$V_{RWM}=5V, T=25°C$		0.1	0.5	μA
Peak Pulse Current	I_{PP}	$t_p = 8/20\mu s$			4	A
Clamping Voltage	V_C	$I_{PP}=4A, t_p=8/20\mu s$		21	25	V
Junction Capacitance	C_j	$V_R = 0V, f = 1MHz$		0.2	0.26	pF

Electrical Parameters (TA = 25 °C unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current



Note: 8/20μs pulse waveform.



Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

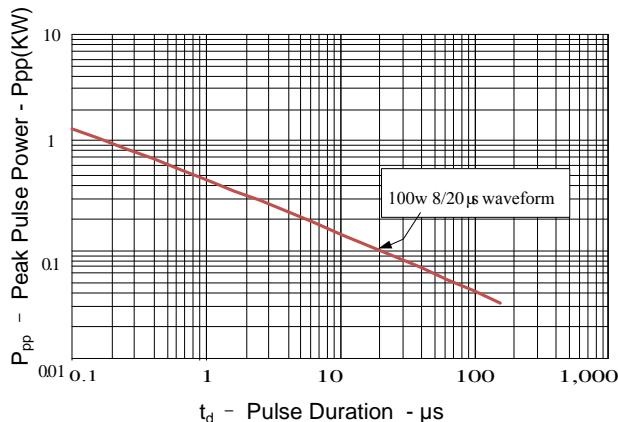


Figure 2: Power Derating Curve

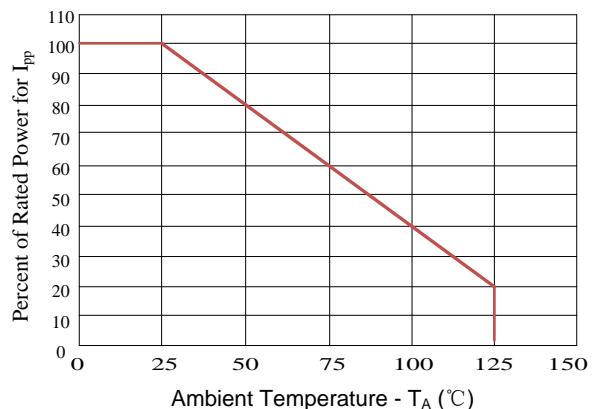


Figure 3: Pulse Waveform

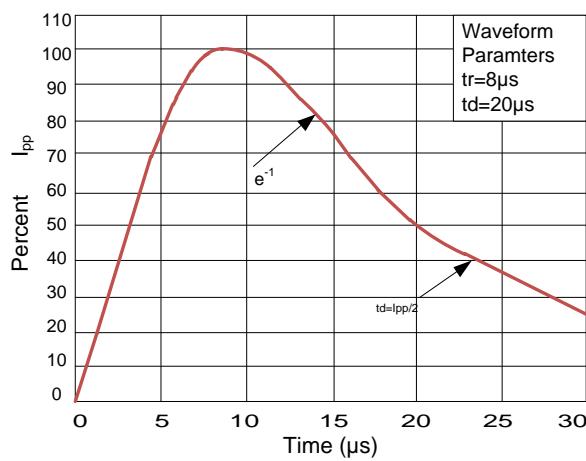
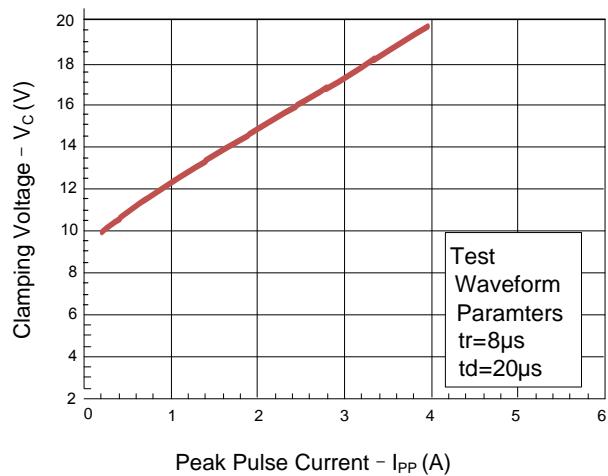


Figure 4: Clamping Voltage vs.Ipp

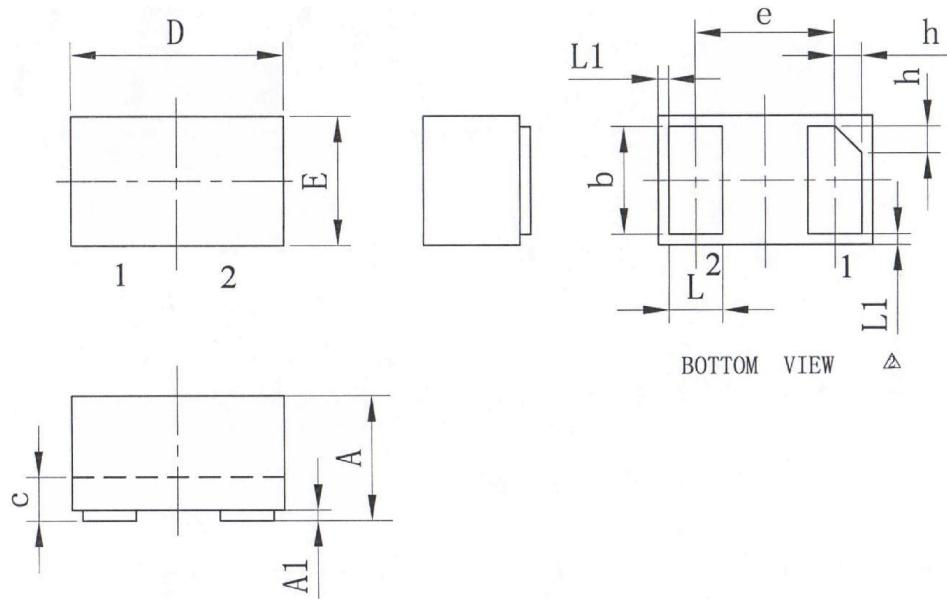




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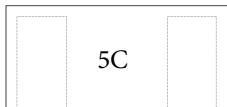
RHTVSUC0521N-T

Outline Drawing – DFN1006



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	0.45	0.50	0.55
A1	0	0.02	0.05
b	0.45	0.50	0.55
c	0.12	0.15	0.18
D	0.95	1.00	1.05
e	0.65BSC		
E	0.55	0.60	0.65
L	0.20	0.25	0.30
L1	0.05REF		
h	0.07	0.12	0.17
载体尺寸 (Mil)	20*20		

Marking



Ordering information

Order code	Package	Base qty	Delivery mode
RHVTVSUC0521N-S	DFN1006	10k	Tape and reel